

	Ref #	Search Text
74	S74	"LDMOS" (lateral near3 diffus\$3 near5 (transistor gate electrode)) "DEMOS" (drain near3 extend\$3 near4 (transistor gate electrode))
75	S75	"CMOS" "PMOS" "NMOS" ("P" near3 (metal adj3 semiconductor)) ("N" near3 (metal adj3 semiconductor))
76	S76	("20020009790" "20020030238" "20020089790" "20030141559" "20040046226" "20040180485" "20040238913" "6160289" "6384643" "6400126" "6642697" "6855985").PN.
77	S77	S74 same S75
78	S78	@ad<= "20031103" or @rlad<= "20031103"
79	S79	S77 and S78
80	S80	("P" near3 body) same ("P" near3 well) ("N" near3 well)
81	S81	("P" near3 body) same (("P" near3 well) ("N" near3 well) well)
82	S82	S81 and S79
83	S83	(438/202).CCLS.
84	S84	(438/204).CCLS.
85	S85	(438/223).CCLS.
86	S86	(438/224).CCLS.
87	S87	(438/227).CCLS.
88	S89	(438/278).CCLS.

	<b>DBs</b>
<b>74</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>75</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>76</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>77</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>78</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>79</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>80</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>81</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>82</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>83</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>84</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>85</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>86</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>87</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>88</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>

	<b>Ref #</b>	<b>Search Text</b>
<b>89</b>	<b>S90</b>	<b>(438/527).CCLS.</b>
<b>90</b>	<b>S88</b>	<b>(438/275).CCLS.</b>

	<b>DBs</b>
<b>89</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>
<b>90</b>	<b>US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB</b>